# NSN 5961-01-040-3682

Transistor - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-040-3682

**Inclosure Material:** 

Metal

**Overall Length:** 

0.375 inches

#### **Overall Diameter:**

0.875 inches

## **Mounting Facility Quantity:**

2

#### Internal Configuration:

Junction contact

#### Electrode Internally-electrically Connected To Case:

Collector

Internal Junction Configuration:

Npn

**Mounting Method:** 

#### Unthreaded hole

**Features Provided:** 

Hermetically sealed case

#### Semiconductor Material:

Silicon

#### Voltage Rating In Volts Per Characteristic:

120.0 breakdown voltage, collector-to-base, emitter open and 100.0 breakdown voltage, collector-to-emitter, base open and 6.0

breakdown voltage, emitter-to-base, collector open

#### **Current Rating Per Characteristic:**

Between 20.00 amperes source cutoff current and 50.00 amperes source cutoff current

#### **Power Rating Per Characteristic:**

250.0 milliwatts small-signal input power, common-collector

## Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

## **Terminal Type And Quantity:**

2 uninsulated wire lead and 1 case

## **Specification Data:**

80131-release6361 professional/industrial association specification

## Shelf Life:

N/a

# Unit Of Measure:

---

#### Demilitarization:

No

#### Fiig:

A110a0